#### Chapter 6: Bipolar Junction Transistors (BJT) Sections 6.1-6.6

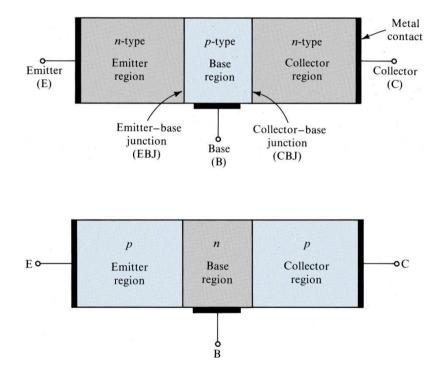
Signal amplification is important in many applications, such as telecommunications. Before the advent of transistors, signal amplification was accomplished using vacuum tubes. Transistors are much smaller and do not need a long warmup time needed with vacuum tubes. The invention of the bipolar junction transistor started a revolution which placed electronics on a path of miniaturization; a fact that would have been impossible with vacuum tubes.

In summary, the transistor and subsequently the integrated circuit must certainly qualify as two of the greatest inventions of the twentieth century.

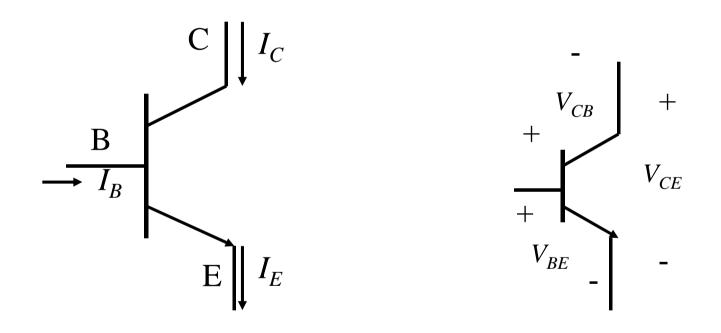
### **BJT** Structure

By placing two PN junctions together we can create a bipolar transistor. A BJT transistor has three terminals. The base (B), the collector (C), and the emitter (E).

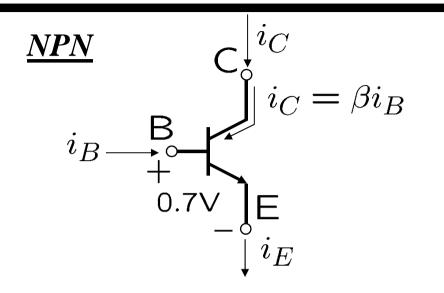
• Transistors are three-terminal devices. The terminals are labelled the base, the emitter and the collector. Each BJTs consist of two *pn* junctions (where a '*p* type' material joins to a 'n type material'). Therefore, a transistor may be made up from a piece of *p* type material sandwiched between two n type regions (*npn*), or it may be made up from a piece of 'n type' material sandwiched between two 'p type' regions (*pnp*)



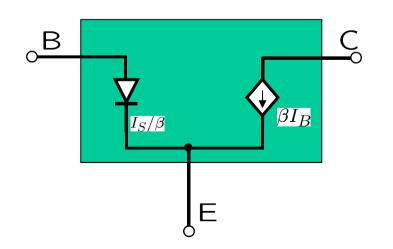
# 3 Currents and 3 Voltages in the BJT *npn* Transistor

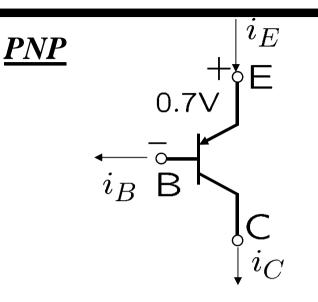


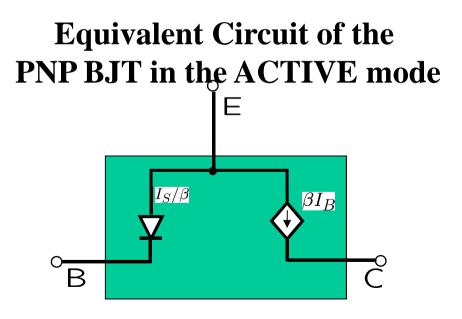
Equivalent circuit of the transistors in the active mode



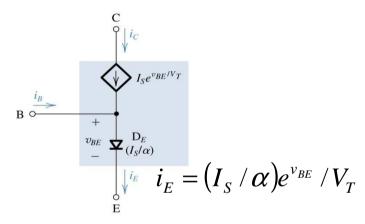
#### Equivalent Circuit of the NPN BJT in the ACTIVE mode





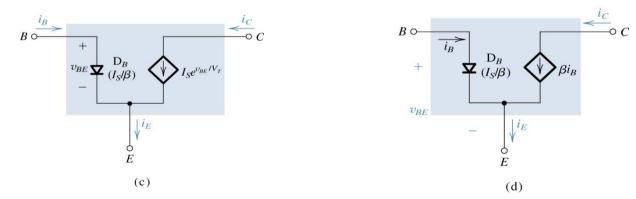


#### Large-Signal Equivalent-Circuit Models of the *npn* BJT operating in the active mode



 $B \stackrel{i_{B}}{\longrightarrow} + \underbrace{i_{E} \bigvee \bigtriangledown_{(I_{S}/\alpha)}}_{E}$ (b) Current - controlled Current Source

Voltage-controlled Current Source)



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$$i_{C} = I_{s}e^{v_{BE}/V_{T}}$$

$$i_{B} = \frac{i_{C}}{\beta} = \left(\frac{I_{S}}{\beta}\right)e^{v_{BE}/V_{T}}$$

$$i_{E} = \frac{i_{C}}{\alpha} = \left(\frac{I_{S}}{\alpha}\right)e^{v_{BE}/V_{T}}$$

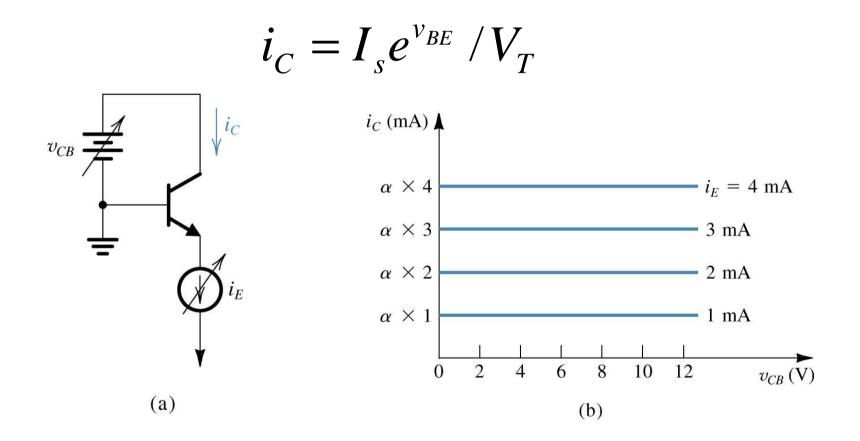
$$i_{C} = \alpha i_{E}; i_{B} = (1-\alpha)i_{E} = \frac{i_{E}}{\beta+1}$$

$$i_{C} = \beta i_{B}; i_{E} = (\beta+1)i_{B}$$

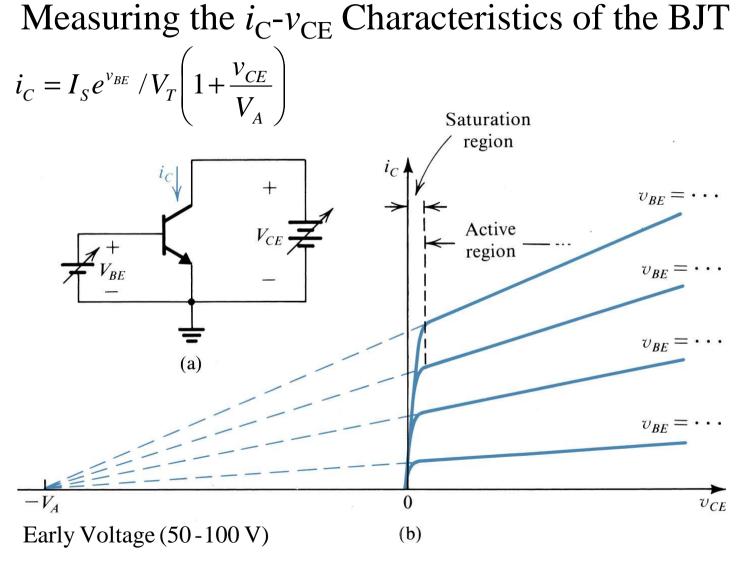
$$\beta = \frac{\alpha}{1-\alpha}$$

- The basic principle involves the use of the voltage between two terminals to control the current flowing in the third terminal.
- Current is conducted by both electrons and holes, therefore the name bipolar.
- $\alpha$  is called the common-base current gain.
- $\beta$  is called the common-emitter current gain.

The  $i_{\rm C}$ - $v_{\rm CB}$  Characteristics of an *npn* Transistor



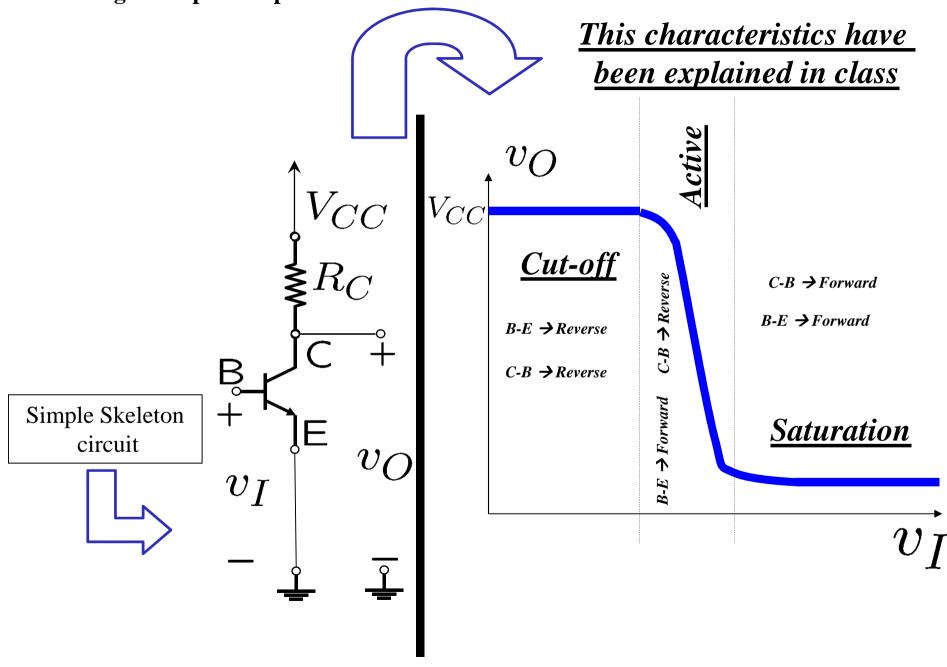
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## Amplification in BJT:

- 1. We first derive the Input/Output transfer characteristics of a "*skeleton*" BJT circuit.
- 2. Then we see, on a qualitative basis, how those characteristics can be used in the amplification.
- 3. After that we *"calculate"* the actual voltage amplification factor.
- 4. Finally, we develop a systematic approach that will be used to analyze/design more complicated and general amplifier circuits.



1.Deriving the Input/Output transfer characteristics of a "skeleton" BJT circuit.

2. Then we see, on a qualitative basis, how those characteristics can be used in the amplification.

